TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT4S03A

VHF~UHF Band Low Noise Amplifier Applications

• Low noise figure: NF = 1.4dB (f = 2 GHz)

• High gain: Gain = 9dB (f = 2 GHz)

Absolute Maximum Ratings (Ta = 25°C)

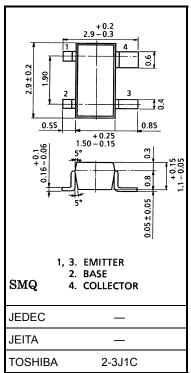
Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	10	V
Collector-emitter voltage	V _{CEO}	5	V
Emitter-base voltage	V_{EBO}	2	V
Base current	IC	40	mA
Collector current	ΙΒ	10	mA
Collector power dissipation	PC	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

cations Unit: mm



Weight: 0.012 g (typ.)

Marking



Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency —	f _T (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	2	4.5	_	GHz
	f _T (2)	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	7	10	_	
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	3.5	5.5	_	dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	7	9	_	
Noise figure ———	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_C = 7 \text{ mA}, f = 2 \text{ GHz}$		1.4	2.2	ub

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V, } I_C = 0$	_	_	1	μА
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}$	80	_	160	
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note)	_	0.7	1.05	pF

Note: Cre is measured by 3 terminal method with capacitance bridge.

Caution

This device is sensitive to electrostatic discharge. Please handle with caution.

RESTRICTIONS ON PRODUCT USE

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
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